

THE RADIATION DEFECT INFLUENCE ON  
OXYGEN PRECIPITATION IN THERMALLY  
TREATED SILICON

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S u m m a r y

Oxygen precipitation in neutron-irradiated and thermally treated silicon crystals is studied by varying neutron fluence ( $10^{15} - 10^{19}$  neutr./cm<sup>2</sup>) and annealing temperature (600 - 1000 °C). IR spectroscopy and selective etching were used for the investigation. It is found that the precipitation process was accelerated in irradiated silicon in a wide temperature range. The precipitation rate has become weakly dependent on annealing temperature with the fluence increasing above  $5 \cdot 10^{16}$  neutr./cm<sup>2</sup>. These effects clearly show the main role of radiation point defects in oxygen precipitation.